Amendments to the Specification:

Please amend the specification as follows::

Page 5, fifth paragraph

FIG. 1D is a sectional view illustrating a fourth step in the method of constructing the lancet device with the nitride film ~~16d~~**14d** and the photoresist **16d** being etched away leaving strips of uncovered bare silicon wafer;

Page 5, seventh paragraph

FIG. 1F is a sectional view illustrating the method of constructing the lancet device in accordance with the present invention with ~~approximately 50 micrometers and approximately 100 micrometers~~ areas of thinned silicon wafer being exposed after the fifth step;

Page 7, third paragraph

As illustrated in **FIG. 1E**, the uncovered areas of the silicon wafer **12e** are etched away in bulk by potassium hydroxide (KOH). Etching the silicon wafer **12e** with potassium hydroxide results in between ~~approximately 50 micrometers and approximately 100 micrometers of the silicon wafer **12e**~~ areas of thinned silicon wafer being exposed, as illustrated in **FIG. 1F**. Next, as illustrated in **FIG. 1G**, a photoresist coating **18g** is applied to the silicon wafer **12g**. Then, as illustrated in **FIG. 1H**, the silicon wafer **12h** is patterned and exposed and the lancet devices **10h** are "punched" out using a plasma etching process. Plasma etching provides excellent control of the shape of the microlancet without forming weak spots. Finally, as illustrated in **FIG. 1I**, the photoresist coating **18h** is removed resulting in a silicon lancet device with a nitride-covered base.

Page 8, third paragraph, Page 9, first paragraph

Disposable microlancet device **30i** (see **FIG. 3A**) may be employed for obtaining a blood sample through the skin of a subject. The device is formed by an elongated single crystal silicon substrate **32a** having base end **30b** and penetration end **30p**. Base portion **32b** formed at the base end of the silicon substrate permits the device to be retained during penetration and sampling. Penetration portion **32p** formed at the penetration end has smooth continuous profile and terminates in a sharp point with smooth continuous cutting profile.

The smooth profile permits easy piercing and penetration of the skin in order to obtain a blood sample while inflicting minimum pain on the subject. The penetration portion has a thickness cross-section dimension "T" (see FIG.s **3B and 3C**) and a width cross section dimension "W" (see **FIG.s 3A and 3C**). The cross-section may be any suitable shape such as rhombic or rectangular as shown in **FIG. 3C**. The thickness dimension **T** of the base portion may extend from about 50 micrometers to about 250 micrometers ~~excluding the sharp point~~. The width dimension W of the base portion may extend from about 50 micrometers to about 250 micrometers excluding the point. At least one of these dimensions may taper toward the penetration end to form the ~~sharp~~ point (see **FIG. 3A**). The silicon substrate may have a length diameter "L" (see **FIG. 3B**) of about 1 millimeter to about 3 millimeters, Silicon nitride film 34 may extend over at least part of the base portion.